(54) **SEMICONDUCTOR MEMORY DEVICE**

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(57)   **ABSTRACT**

A semiconductor memory device includes a first wiring to a
fifth wiring, a plurality of memory cells disposed between
the wirings, and a first contact electrode to a third contact
electrode. The first contact electrode is disposed between the
first wiring and the fifth wiring, and is electrically connected
to the first wiring and the fifth wiring. The second contact
electrode is disposed between the first contact electrode and
the fifth wiring, and is electrically connected to the first
wiring and the fifth wiring. The third contact electrode is
disposed between the second contact electrode and the fifth
wiring, and is electrically connected to the first wiring and
the fifth wiring. The second contact electrode has a width
larger than a width of the first contact electrode and larger
than a width of the third contact electrode.